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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD49815TF

Digital Camera Signal Processor



ADE-207-316 (Z)
1st Edition
Sep. 1999

Description

The HD49815TF is a CMOS IC that has been developed as a digital signal-processing IC for CCD-camera digital-signal-processing systems.

Functions

- CCD-sensor drive-pulse generation (TG)
- Digital AGC (automatic gain control)
- Color signal separation circuit
- RGB matrix
- RGB gain
- RGB and Y gamma
- Color-difference matrix
- Enhancer
- RGB and Y setup
- Digital I/F (4:2:2)
- Zoom control
- Mirror reversal
- Synchronization signal generator for encoding (SSG)
- AWB, AE, and AF detection
- Two-channel 8-bit D/A converter

Features

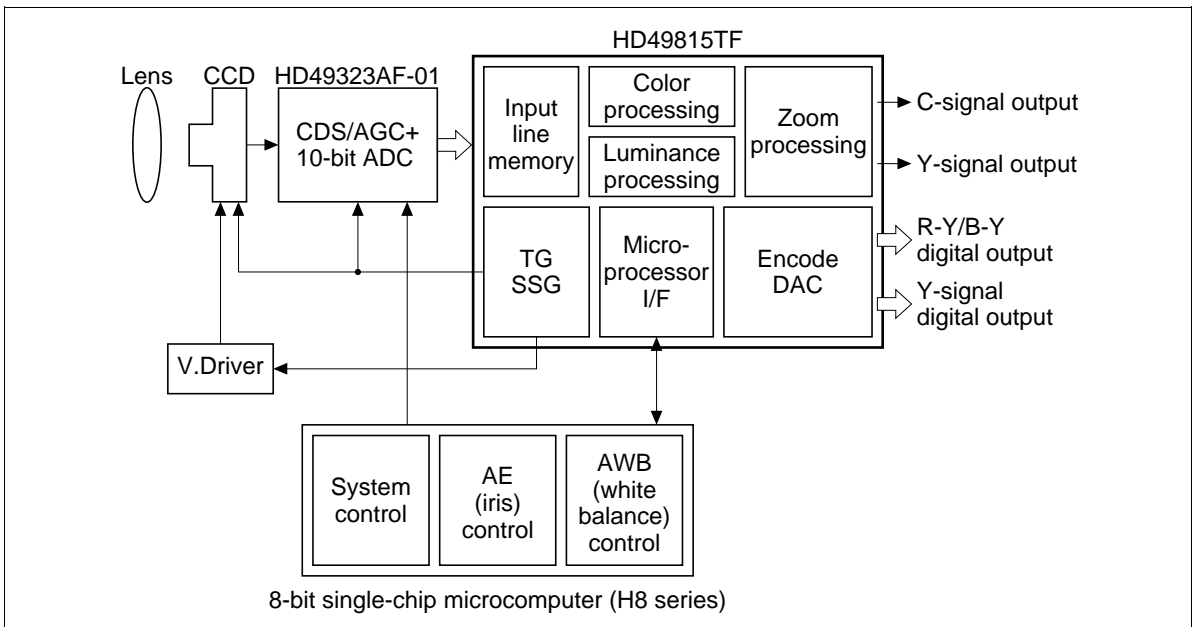
- The HD49815TF provides camera-signal processing, TG, SSG, zoom, and D/A functions and other functions in a single chip and supports high system-integration level.
- In conjunction with the HD49323AF-01 (CDS/AGC + 10-bit ADC) and the control microcomputer, the HD49815TF forms a three-chip kit that can implement an optimal CCD-camera digital-signal-processing system.
- The HD49815TF provides the zoom function and controls the 1- to 256- times linear zoom. It also provides the half-mirror function.

HD49815TF

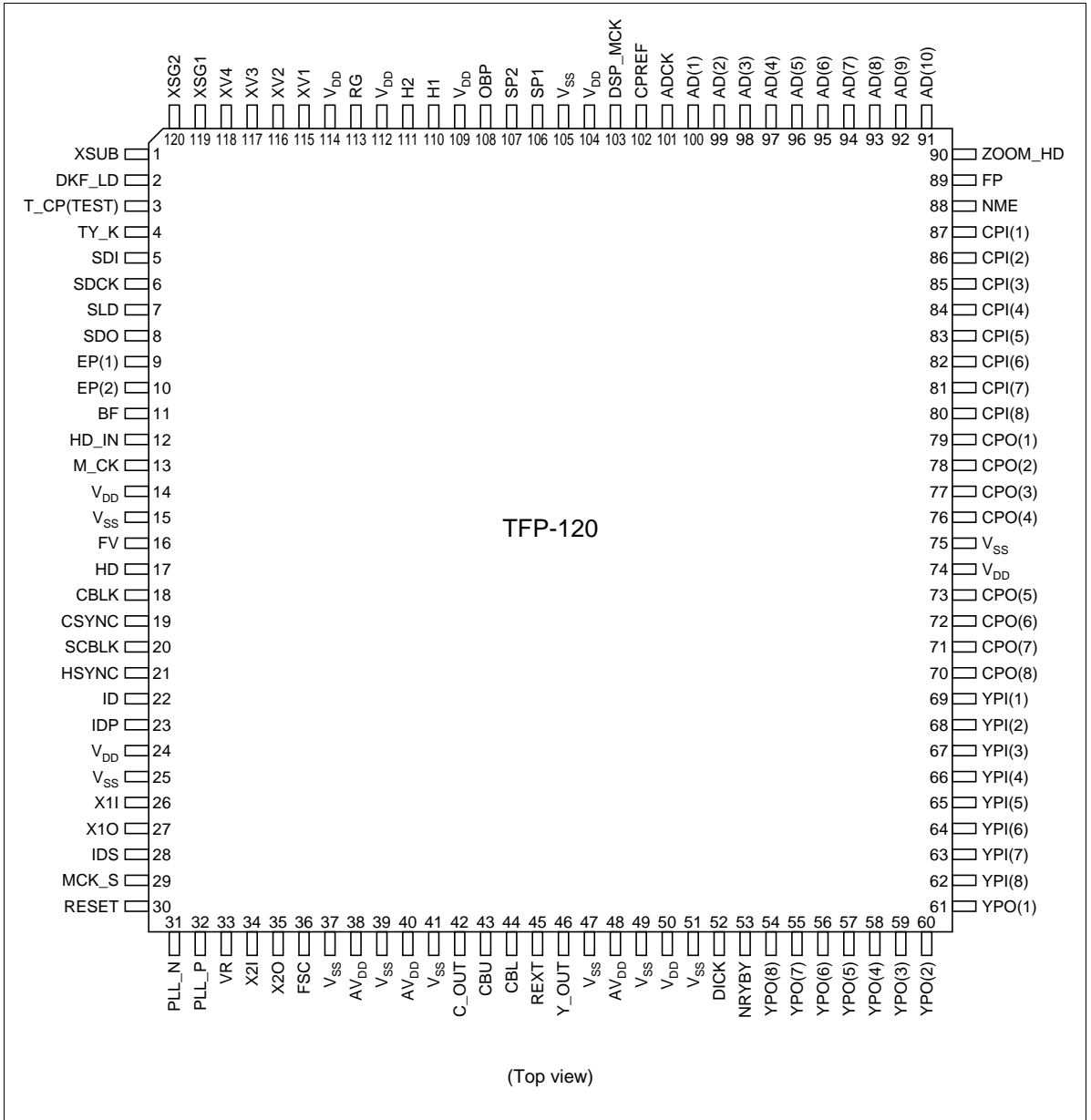
Features (cont)

- Since the HD49815TF can be made compatible with the former product, HD49811TFA, through software, a shorter development term is enabled.
- Since software controls AWB, AE, and AF, any protocol can be prepared according to the camera shooting conditions.
- Programmable TG enables use of any CCD device.

System Block Diagram



Pin Arrangement



Pin Description

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
1	XSUB	CCD shutter pulse	O	CCD control pulse	ZC2R
2	DKF_LD	Line input LD	I	Line input dedicated load	ICS
3	T_CP	Test	I	Test pin (GND input)	IC
4	TY_K	Title SW	I	Title-killer SW (1 = On, 0 = Off)	ICD
5	SDI	State data input	I	State data-setting data input	IC
6	SDCK	State data clock	I	State data-setting clock	ICS
7	SLD	State data load pulse	I	State data-latch pulse	ICS
8	SDO	AWB, AE, data output	O	AWB, AE, and AF detection-data output	ZC2R
9	EP (1)	AE window pulse 1	O	Iris detection-area-setting pulse: SP-A7 [8] output changeover	ICZC2R
10	EP (2)	AE window pulse 2	O	Iris detection-area-setting pulse: SP-A7 [8] output changeover	ICZC2R
11	BF	Burst flag	O	Burst flag output	ICZC2R
12	HD_IN	External CSYNC input	I	External CSYNC input	ICSD
13	M_CK	Microprocessor clock	O	Microprocessor clock output (1/2 or 1/4 dividing of X'tal 1)	OC2R
14	V _{DD}	V _{CC2}	—	3.3 V power supply	VCCI
15	V _{SS}	GND	—	GND	GNDI
16	FV	Field vertical output	O	Vertical synchronization pulse	ICZC2R
17	HD	HD output	O	Horizontal synchronization pulse	ICZC2R
18	CBLK	Blanking pulse	O	Blanking pulse	ICZC2R
19	CSYNC	SYNC output	O	SYNC pulse	ICZC2R
20	SCBLK	SC blanking pulse	O	Subcarrier blanking pulse (SECAM)	ICZC2R
21	HSYNC	Horizontal SYNC	O	Horizontal SYNC pulse (SECAM)	OC2R
22	ID	Identity	O	SECAM determination pulse	OC2R
23	IDP	Identity pulse	O	SECAM determination pulse	ICZC2R
24	V _{DD}	V _{CC2}	—	3.3 V power supply	VCCC
25	V _{SS}	GND	—	GND	GNDC
26	X1I	X'tal 1 input	I	2fsc oscillator input	IQ3
27	X1O	X'tal 1 output	O	2fsc oscillator output	OQ3
28	IDS	Line ID reset input	I	Line-determination-signal input	ICD
29	MCK_S	MCK output SW	I	Pin 13 MCK dividing setting SW (1 = 1/2, 0 = 1/4)	IC
30	RESET	Reset	I	Reset: to restore the initial data settings	ICS

Pin Description (cont)

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
31	PLL_N	PLL negative	O	PLL signal output	ZC2
32	PLL_P	PLL positive	O	PLL signal output	ZC2
33	VR	Vertical reset	I	Vertical synchronization signal input	ICSD
34	X2I	X'tal 2 input	I	4fsc oscillator input	IQ2
35	X2O	X'tal 2 output	O	4fsc oscillator output	OQ2
36	FSC	Sub carrier frequency	O	fsc output	ICZC2R
37	V _{SS}	GND	—	GND	GND A
38	AV _{DD}	Analog V _{CC2}	—	Analog system power supply: 3.3 V	VCCA
39	V _{SS}	GND	—	GND	GND A
40	AV _{DD}	Analog V _{CC2}	—	Analog system power supply: 3.3 V	VCCA
41	V _{SS}	GND	—	GND	GND A
42	C_OUT	C analog signal output	O	Chrominance-signal analog output	OA
43	CBU	Current buffer upper	I	D/A upper current source	IA
44	CBL	Current buffer lower	I	D/A lower current source	IA
45	REXT	Reference resister EXT	I	Reference voltage input	IA
46	Y_OUT	Y analog signal output	O	Luminance-signal analog output	OA
47	V _{SS}	GND	—	GND	GND A
48	AV _{DD}	Analog V _{CC2}	—	Analog system power supply: 3.3 V	VCCA
49	V _{SS}	GND	—	GND	GND A
50	V _{DD}	V _{CC2}	—	Digital system power supply: 3.3 V	VCCI
51	V _{SS}	GND	—	GND	GND I
52	DICK	Digital interface clock	O	Digital interface clock output	ICZC2R
53	NRYBY	R-Y, B-Y phase output	O	Color-difference signal phase clock	ICZC2R
54	YPO (8)	Y parallel output (8); MSB	O	Luminance-signal digital output MSB	OC2R
55	YPO (7)	Y parallel output (7)	O	Luminance-signal digital output	OC2R
56	YPO (6)	Y parallel output (6)	O	Luminance-signal digital output	OC2R
57	YPO (5)	Y parallel output (5)	O	Luminance-signal digital output	OC2R
58	YPO (4)	Y parallel output (4)	O	Luminance-signal digital output	OC2R
59	YPO (3)	Y parallel output (3)	O	Luminance-signal digital output	OC2R
60	YPO (2)	Y parallel output (2)	O	Luminance-signal digital output	OC2R
61	YPO (1)	Y parallel output (1) ; LSB	O	Luminance-signal digital output LSB	OC2R
62	YPI (8)	Y parallel input (8); MSB	I	Luminance-signal digital input MSB	ICD
63	YPI (7)	Y parallel input (7)	I	Luminance-signal digital input	ICD
64	YPI (6)	Y parallel input (6)	I	Luminance-signal digital input	ICD

Pin Description (cont)

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
65	YPI (5)	Y parallel input (5)	I	Luminance-signal digital input	ICD
66	YPI (4)	Y parallel input (4)	I	Luminance-signal digital input	ICD
67	YPI (3)	Y parallel input (3)	I	Luminance-signal digital input	ICD
68	YPI (2)	Y parallel input (2)	I	Luminance-signal digital input	ICD
69	YPI (1)	Y parallel input (1); LSB	I	Luminance-signal digital input LSB	ICD
70	CPO (8)	C parallel output (8); MSB	O	Chrominance-signal digital output MSB	OC2R
71	CPO (7)	C parallel output (7)	O	Chrominance-signal digital output	OC2R
72	CPO (6)	C parallel output (6)	O	Chrominance-signal digital output	OC2R
73	CPO (5)	C parallel output (5)	O	Chrominance-signal digital output	OC2R
74	V _{DD}	V _{CC2}	—	3.3 V power supply	VCCO
75	V _{SS}	GND	—	GND	GND0
76	CPO (4)	C parallel output (4)	O	Chrominance-signal digital output	OC2R
77	CPO (3)	C parallel output (3)	O	Chrominance-signal digital output	OC2R
78	CPO (2)	C parallel output (2)	O	Chrominance-signal digital output	OC2R
79	CPO (1)	C parallel output (1); LSB	O	Chrominance-signal digital output LSB	OC2R
80	CPI (8)	C parallel input (8); MSB	I	Chrominance-signal digital input MSB	ICD
81	CPI (7)	C parallel input (7)	I	Chrominance-signal digital input	ICD
82	CPI (6)	C parallel input (6)	I	Chrominance-signal digital input	ICD
83	CPI (5)	C parallel input (5)	I	Chrominance-signal digital input	ICD
84	CPI (4)	C parallel input (4)	I	Chrominance-signal digital input	ICD
85	CPI (3)	C parallel input (3)	I	Chrominance-signal digital input	ICD
86	CPI (2)	C parallel input (2)	I	Chrominance-signal digital input	ICD
87	CPI (1)	C parallel input (1); LSB	I	Chrominance-signal digital input LSB	ICD
88	NME	Memory HD output	O	Line memory control output	ICZC2DR
89	FP	Field pulse	O	Field pulse	ICZC2R
90	ZOOM_HD	Zoom HD output	O	Horizontal synchronization signal	ICZC2R
91	AD (10)	AD input (10); MSB	I	A/D data input MSB	IC
92	AD (9)	AD input (9)	I	A/D data input	IC
93	AD (8)	AD input (8)	I	A/D data input	IC
94	AD (7)	AD input (7)	I	A/D data input	IC

Pin Description (cont)

Pin No.	Symbol	Pin Name	I/O	Description	I/O Format
95	AD (6)	AD input (6)	I	A/D data input	IC
96	AD (5)	AD input (5)	I	A/D data input	IC
97	AD (4)	AD input (4)	I	A/D data input	IC
98	AD (3)	AD input (3)	I	A/D data input	IC
99	AD (2)	AD input (2)	I	A/D data input	IC
100	AD (1)	AD input (1); LSB	I	A/D data input LSB	IC
101	ADCK	AD clock	O	A/D converter clock	ICZC2R
102	CPREF	Clamp reference output	O	Clamp reference pulse	2C3
103	DSP_MCK	Microprocessor clock output	O	Microprocessor clock output: SP-A7 [8] output changeover	ICZC2R
104	V _{DD}	V _{CC2}	—	3.3 V power supply	VCCO
105	V _{SS}	GND	—	GND	GNDO
106	SP1	Sampling pulse 1	O	Sampling pulse for the AGC/CDS IC	ICZC2
107	SP2	Sampling pulse 2	O	Sampling pulse for the AGC/CDS IC	ICZC2
108	OBP	OBP pulse	O	Optical black-pulse output	ICZC2R
109	V _{DD}	V _{CC1}	—	3 V or 5 V power supply (H1/H2 power supply)	VCCC35
110	H1	H1	O	CCD-sensor horizontal drive pulse	OC3R
111	H2	H2	O	CCD-sensor horizontal drive pulse	OC3R
112	V _{DD}	V _{CC1}	—	5 V power supply (RG power supply)	VCCC5
113	RG	Reset gate	O	CCD-sensor control reset gate	ZC3R
114	V _{DD}	V _{CC2}	—	3.3 V power supply	VCCO
115	XV1	XV1	O	CCD-sensor vertical control pulse	ICZC2R
116	XV2	XV2	O	CCD-sensor vertical control pulse	ICZC2R
117	XV3	XV3	O	CCD-sensor vertical control pulse	ICZC2R
118	XV4	XV4	O	CCD-sensor vertical control pulse	ICZC2R
119	XSG1	XSG1	O	CCD-sensor vertical control pulse	ZC2R
120	XSG2	XSG2	O	CCD-sensor vertical control pulse	ZC2R

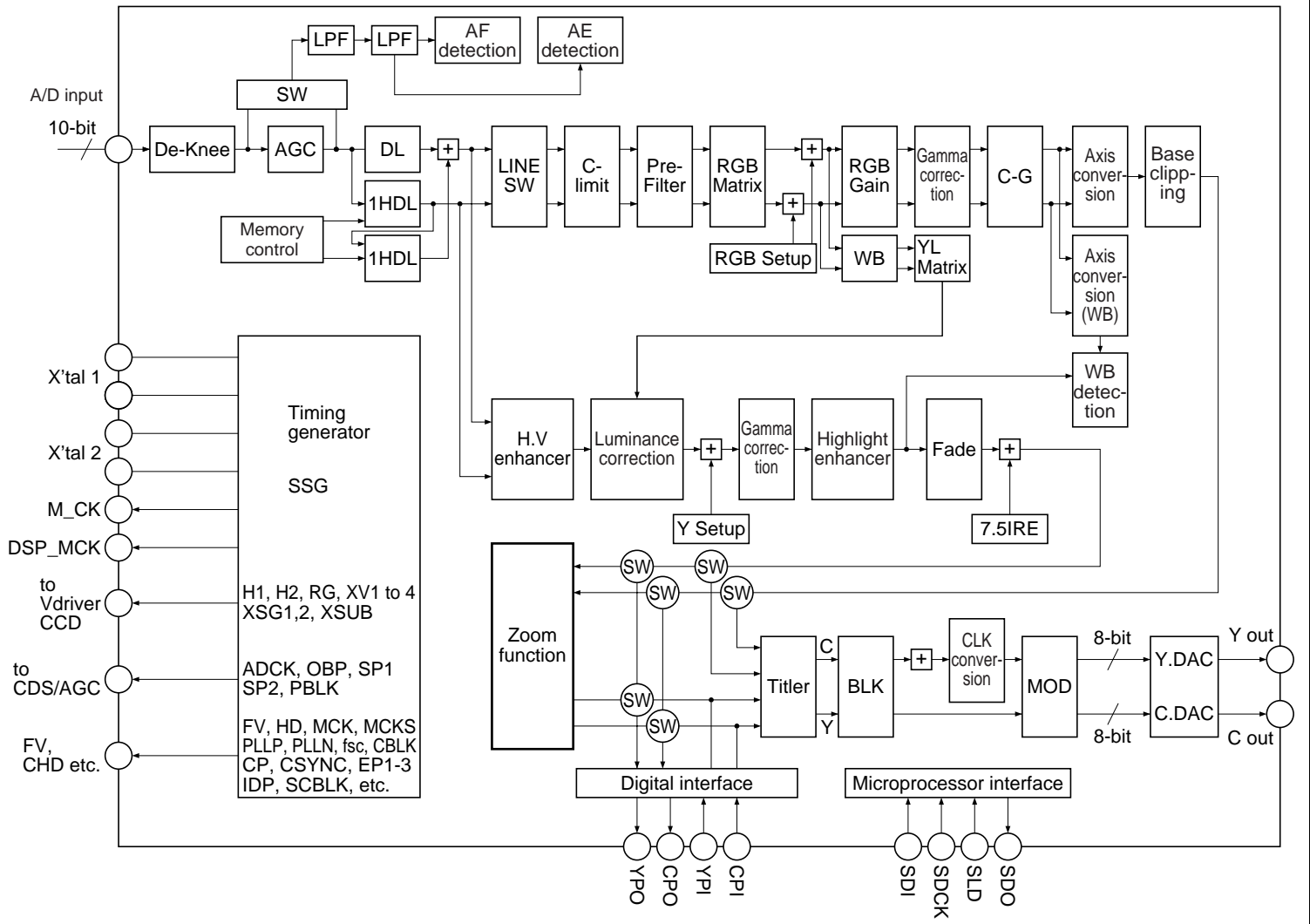
Description of I/O Format

I/O Format	Contents
IC	CMOS level input
ICD	CMOS level input with pull-down resistor
ICS	CMOS level schmitt input
ICSD	CMOS level input with pull-down resistor
ICZC2	CMOS level common I/O (4 mA)
ICZC2DR	CMOS level common I/O with pull-down resistor and through-put control (4 mA)
ICZC2R	CMOS level common I/O with through-put control (4 mA)
OC2R	CMOS level output with through-put control (4 mA)
OC3R	CMOS level output with through-put control (8 mA)
IQ2	Crystal oscillator input
OQ2	Crystal oscillator output
IQ3	Crystal oscillator input
OQ3	Crystal oscillator output
ZC2	CMOS-level three-state output (4 mA)
ZC2R	CMOS-level three-state output with through-put control (4 mA)
ZC3	CMOS-level three-state output (8 mA)
ZC3R	CMOS-level three-state output with through-put control (8 mA)
VCCI	Core system power supply: 3 V
VCCO	Puddling system power supply: 3 V
VCCC	Common power supply: 3 V
VCCC5	Common power supply: 5 V for pin 112
VCCC35	Common power supply: 3 or 5 V for pin 109
GNDI	Core system GND
GNDO	Puddling system GND
GNDC	Common GND
IA	Analog input
OA	Analog output
VCCA	Analog power supply
GND A	Analog GND

Notes: 1. Pin 113 is used for 5 V system output.

2. Pins 110 and 111 are used for 3 V or 5 V system output. They depend on the voltage of pin 109.

Block Diagram



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item		Symbol	Ratings	Unit
Power supply voltage		V_{cc}	-0.2 to +6.8	V
Pin voltage (5 V operation block)		V_{t5V}	-0.2 to $V_{cc1} + 0.2$	V
Pin voltage (3 V operation block)		V_{t3V}	-0.2 to $V_{cc2} + 0.2$	V
Output current	Per output	I_o	-32 to +32	mA
	Per GND- V_{cc} pair	I_{ot}	-72 to +72	mA
Allowable power dissipation		P_{opr}	450	mW
Operating temperature		T_{opr}	-10 to +75	$^\circ\text{C}$
Storage temperature	With bias	T_{bias}	-10 to +75	$^\circ\text{C}$
	Without bias	T_{stg}	-40 to +125	$^\circ\text{C}$

Notes: 1. Using this LSI at values in excess of the absolute maximum ratings may permanently damage the LSI. The LSI should normally be operated under the conditions specified for the electrical characteristics. Exceeding these conditions may lead to incorrect operation and may adversely affect LSI reliability.

2. All voltage values are referenced to GND = 0 V.

3. The pin voltage ratings also apply to the NC pins.

4. V_{cc1} indicates the 5 V system power supply and V_{cc2} indicates the 3 V system power supply.

Electrical Characteristics ($V_{CC1} = 4.75\text{ V to }5.25\text{ V}$, $V_{CC2} = 2.85\text{ V to }3.15\text{ V}$,
 $AV_{CC} = 2.85\text{ V to }3.15\text{ V}$, $T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
							Note
CMOS-level	V_{IHC}	$V_{CC2} \times 0.75$	—	V_{CC2}	V		
input voltage	V_{ILC}	0.0	—	$V_{CC2} \times 0.20$	V		
CMOS schmitt	V_{TC+}	2.50	—	V_{CC2}	V	$V_{CC1} = 5\text{ V}$	
input voltage	V_{TC-}	0.0	—	0.60	V	$V_{CC2} = 3\text{ V}$	
Output voltage	V_{OHC1}	$V_{CC1} - 0.5$	—	—	V	$I_{OH} = -200\ \mu\text{A}$ 5 V system pin	1
	V_{OLC1}	—	—	0.4	V	$I_{OL} = 200\ \mu\text{A}$ 5 V system pin	
	V_{OHC2}	$V_{CC2} - 0.5$	—	—	V	$I_{OH} = -200\ \mu\text{A}$ 3 V system pin	1, 5
	V_{OLC2}	—	—	0.4	V	$I_{OL} = 200\ \mu\text{A}$ 3 V system pin	1, 6
Input leakage current	I_{LI}	—	—	1.0	μA	$V_{IN} = 0\text{ V to }V_{CC}$	2
Output leakage current	I_{LO}	—	—	1.0	μA	Output Hi-Z conditions	2
Pull-down current	I_{PD}	5	—	100	μA	$V_{IN} = V_{CC2} = 3\text{ V}$	
Power dissipation	Popr	—	—	450	mW	$V_{CC1} = 5\text{ V}$, $V_{CC2} = 3\text{ V}$, $AV_{CC} = 3\text{ V}$	3
Analog output voltage (full scale)	Vfull	0.80	1.00	1.20	V		3, 4
Analog output voltage (zero scale)	Vzero	-0.20	0.00	0.20	V		
Differential linearity	DNL	-2.0	—	2.0	LSB		

- Notes: 1. Output voltage must be measured in the steady state.
2. Except for pins that include a pull-down resistor.
3. Guaranteed at $C_{BU} = 0.1\ \mu\text{F}$, $C_{BL} = 0.1\ \mu\text{F}$, $R_{EXT} = 3.4\ \text{k}\Omega$, analog output load resistance = $500\ \Omega$, and $T_a = 25^\circ\text{C}$.
4. Applied to pins indicated as OA in the I/O format column of the pin-functions table.
5. Because V_{OH} of pin 31 cannot be measured logically, it was not tested.
6. Because V_{OL} of pin 32 cannot be measured logically, it was not tested.
7. V_{CC1} , V_{CC2} , and AV_{CC} indicate the 5 V system power supply, the 3 V system power supply, and the analog system power supply, respectively. V_{CC} indicates V_{CC1} , V_{CC2} , and AV_{CC} .
8. The voltage range of pin 109 (VCCC35) is $V_{CC} = 2.85\text{ V to }5.25\text{ V}$.

Crystal Oscillation Circuit

1. Measuring conditions

The oscillation frequency was measured under the following conditions.

$$V_{CC1} = 5.0 \text{ V}$$

$$V_{CC2} = 3 \text{ V}$$

$$T_a = 25^\circ\text{C}$$

8 MHz, 20 MHz, and 24 MHz:

$$R_f = 1 \text{ to } 10 \text{ M}\Omega$$

$$C_{in}, C_{out} = 20 \text{ pF } (\pm 20 \text{ pF})$$

32 MHz:

$$R_f = 1 \text{ to } 10 \text{ M}\Omega$$

$$C_{in} = 20 \text{ pF } (\pm 20 \text{ pF})$$

$$C_{out} = 100 \text{ pF } (\pm 20 \text{ pF}), C_o = 15 \text{ pF } (\pm 5 \text{ pF}), L_{out} = 1 \text{ }\mu\text{H}$$

The conditions above may be changed within the range of measuring conditions.

2. Measuring method

Under the measuring conditions above, two methods were tested.

$f_{min.} = 20 \text{ MHz}$, and $f_{max.} = 32 \text{ MHz}$ (applied to pins 26 and 27)

$f_{min.} = 8 \text{ MHz}$, and $f_{max.} = 24 \text{ MHz}$ (applied to pins 34 and 35)

Note: The oscillation start time t_{osc} is max. = 200 ms.

3. Measuring circuit

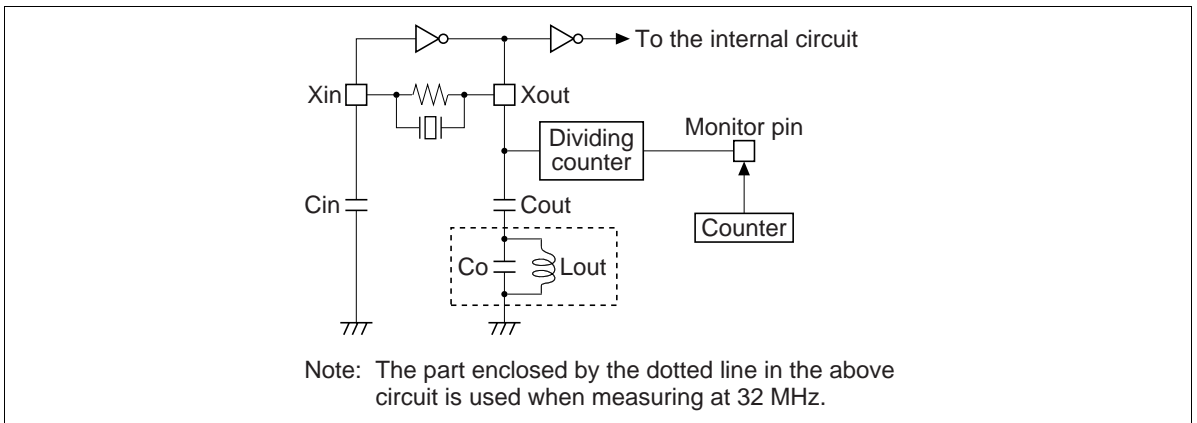


Figure 1 Measuring Circuit

Built-in Functions and System Configuration

System Configuration

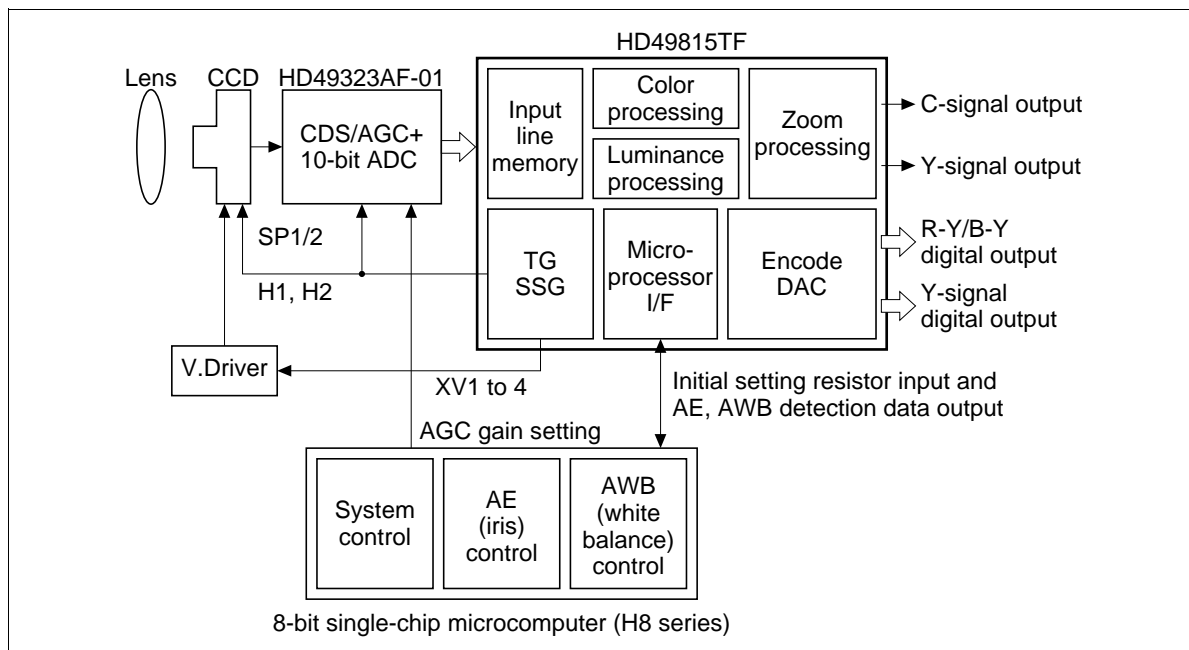


Figure 2 System Configuration

System Description

1. CCD

The following lists the pixels of the CCD sensors that can be used with the HD49815TF. For other pixel numbers, contact our sales dept.

512 (H) × 492 (V) NTSC

512 (H) × 582 (V) PAL

682 (H) × 492 (V) NTSC

681 (H) × 582 (V) PAL

2. CDS/AGC + 10-bit ADC

The HD49323AF-01 (manufactured by Hitachi) is recommended as an optimal CDS/AGC + 10-bit ADC IC for the HD49815TF. Since the HD49323AF-01 provides a correlated double sampling circuit that realizes high S/N and an automatic gain control (AGC) circuit that implements programmable control of 0 dB to 34.7 dB, it enables a high-image-quality camera system when used in conjunction with the HD49815TF.

3. 8-bit single-chip microcomputer

The 8-bit single-chip microcomputer controls the system. It receives the image detection data that the HD49815TF is gathering and implements automatic iris control (AE), automatic white balance control (AWB), and automatic focus control (AF).

When setting the power on, this microcomputer implements the initial setting to the state data of the HD49815TF.

For details on the state data, see “Hitachi Camera DSP (HD49815TF) State Data”.

Built-in Functions

1. Input line memory block

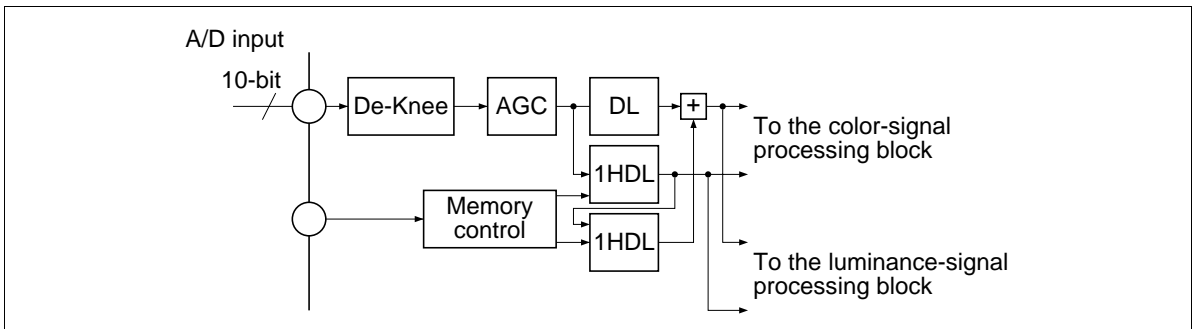


Figure 3 Input Line Memory Block

a. De-knee function

When the CDS/AGC IC at the pre-stage or the external circuit uses the knee circuit to expand the dynamic range of the signal, the de-knee (inverse knee) circuit returns the signal converted by the knee circuit to the original state.

The de-knee point can be set in State Data SP_A0 [1]. The gain of the high-luminance block is 1/2.

b. AGC function

A digital AGC circuit is provided. The AGC gain can be set in State Data SP_A0 [2] from 1 to 16 times.

c. 1H delay line (1HDL) function

This circuit obtains horizontal efficient pixels of the CCD output signal. The number of efficient pixels is set in State Data SP_A0 [9, 10] and TM_A0 [14] MCSET.

2. Color-signal processing block

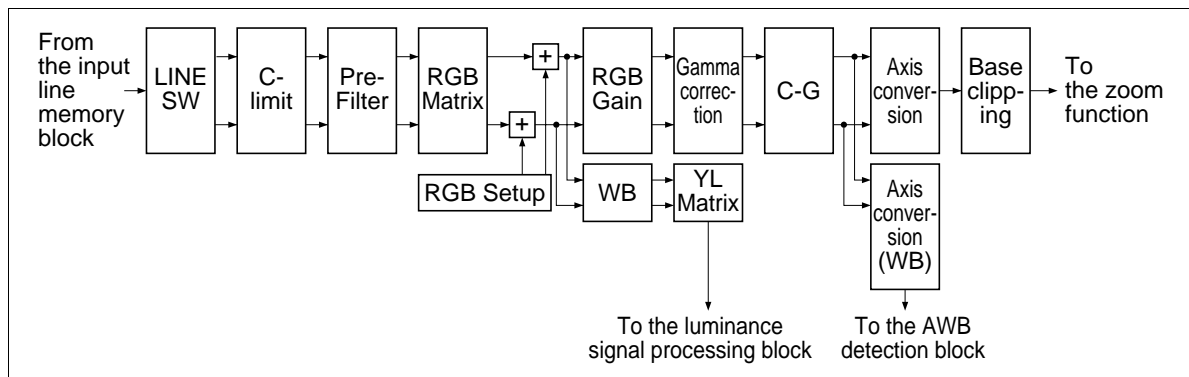


Figure 4 Color-Signal Processing Block

a. C-limit (complementary color clipping level) function

High clipping processing is performed on the complementary color signals independently. High clipping is set in State Data SP_A2 [0 to 3].

The complementary color signal indicates Gb: (G + Cy), Wr: (Ye + Mg), Wb: (Mg + Cy), and Gr: (G + Ye).

b. RGB-matrix block

The three primary colors (red, green, and blue) are acquired in the RGB matrix by multiplying arbitrary coefficients by the four complementary colors (Gb, Wr, Wb, and Gr) and taking the total of those results. The RGB matrix is designed to support the minimum color moire and to enable free color reproduction. Arbitrary coefficients are set in State Data SP_A2 [4 to 15]. The following shows the formula.

$$\begin{pmatrix} R \\ B \\ G \end{pmatrix} = \begin{pmatrix} KRa & KRb & KRc & KRd \\ KBa & KBb & KBc & KBd \\ KGa & KGb & KGc & KGd \end{pmatrix} \begin{pmatrix} Gb \\ Wr \\ Wb \\ Gr \end{pmatrix}$$

↑
State Data SP_A2 [4 to 15]

c. RGB-setup block

The black level of the color signals is variable according to the coefficients of the RGB matrix. The value calculated by the formula below is subtracted from the color signal to correct the black level. The subtracted value can be set externally and is set in State Data SP_A3 [0 to 2].

$$\text{Formula} = -[48 \times \Sigma (\text{Matrix data}) \times 2^3]$$

d. RGB-gain block

The RGB gain value acquired in the AWB control is set in the RGB gain circuit to improve the white reproduction performance. As it is set prior to the gamma correction, it changes the gamma correction amount. The RGB gain can be set in State Data SP_A3 [3 to 5] from 1 to 256 times. (The G gain is set from 1 to 128 times.)

e. C gamma (γ) correction block

The C gamma correction circuit performs gamma processing on the RGB signal. It is set in State Data SP_A3 [6 to 9]. Four kinds of values can be set independently, according to the input-signal level, to acquire optimal gamma characteristics: the C gamma dark (to reduce the gain of the small signals for improving S/N), C gamma coefficient (to control the expansion of the gamma curve), C gamma knee (to decide the slope of the large signals), and C gamma limit (to perform high-clipping processing for the input signal of the C gamma circuit).

f. YL matrix block

The luminance level changes according to the color temperature of the imaged object. Set State Data SP_A5 [12, 13] for the luminance correction. To correct the luminance, create YL from the three primary colors (R, G, and B) and convert it to the luminance signal level. The YL matrix circuit creates the YL level from the RGB signal.

The YL matrix is set in State Data SP_A3 [11 to 13].

g. The axis-conversion (C-Y matrix) block

The C-Y (color-difference) matrix takes R-G and B-G as its input signals, and creates the R-Y and B-Y color-difference signals by setting coefficients for those inputs.

The axis-conversion (C-Y matrix) circuits are set in State Data SP_A8 [0 to 5].

h. Base-clipping block

Since base clipping is performed on the color-difference signals, the base-clipping circuit has the characteristics of clipping the sections near axes on a vector scope.

This circuit is set in State Data SP_A8 [8].

3. Luminance-signal-processing block

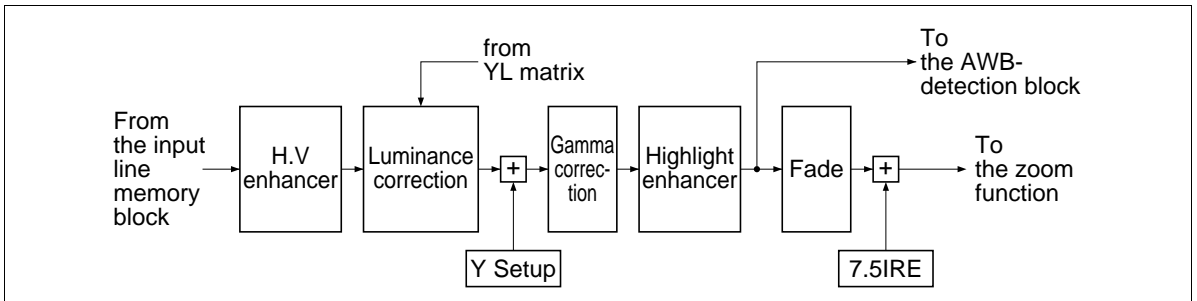


Figure 5 Luminance-Signal-Processing Block

a. H-enhancer function

The H-enhancer circuit allows the core level, the enhancer gain, and the noise coefficient to be set independently to acquire optimal characteristics.

This circuit is set in State Data SP_A4 [4 to 7].

b. V-enhancer function

The V-enhancer circuit allows the enhancer coefficient to be set and can control the gain for only those signal components that exceed the set core level.

This circuit is set in State Data SP_A4 [8 to 10].

- c. Luminance correction

The ratio of the red and blue levels changes according to the color temperature of the imaged object. For example, if a red object is imaged at a low color temperature, the luminance level increases and the object appears to have a lower chrominance. Therefore, the luminance correction circuit performs luminance-correction processing to implement color depth reproduction.

The luminance-correction circuit is set in State Data SP_A5 [12, 13].
 - d. Y setup

Since the OB clamp processes the signal, the black level of the 10-bit signal input to the HD49815TF is fixed to 48/1024. The Y-setup circuit subtracts 48 at the black level. However, when 48 at the black level differs due to the noise mixed in the analog signal, the Y-setup circuit subtracts that value.

The Y-setup circuit is set in State Data SP_A5 [6].
 - e. Gamma correction

The gamma-correction circuit implements the gamma-correction processing for the separated Y signal. Four kinds of values can be set independently, according to the input-signal level, to acquire optimal gamma characteristics: the gamma input limit, the gamma knee coefficient, the gamma coefficient, and the gamma black clipping.

The gamma correction circuit is set in State Data SP_A5 [1 to 4].
 - f. Highlight enhancer

For input-Y signal levels in excess of 100 IRE, the highlight enhancer implements highlight enhancer processing.

This circuit is set in State Data SP_A5 [0, 5, and 14].
 - g. Fade

The fade circuit amplifies the luminance signal by a factor of 0 to 1.

This circuit is set in State Data SP_A5 [9].
4. Zoom, encode block, TG, SSG, and AWB and AE detection blocks
- a. Zoom processing

The Y, R-Y, and B-Y signals completed the color-signal processing and the luminance-signal processing can be electronically zoomed by a factor of 1 to 256.

After clipping CCD signals for V direction, zoom circuit clips these signals for H direction, and expand these signals for H and V directions.

The zooming times and the read starting position for the V and H directions are set in State Data TM_A2 [3, 4, 5, 6, 8, and 9] and ZM_A0 to 6.
 - b. Encode block

This circuit encodes the signals completed the color-signal processing, the luminance-signal processing, and the zoom processing as the NTSC/PAL TV-monitor method.

A DAC that converts the digital signal to an analog signal is provided. The DAC has two channels: one for R-Y signals and one for B-Y signals.

c. TG and SSG

The TG generates the signals required to drive the CCD sensor (H1, H2, RG, SG1/2, and the V transfer pulse), and the CDS/AGC control signals (SP1 and SP2).

In addition, the SSG generates the signals to synchronize with the TV monitor (the Sync signal).

The drive timing of the generated signals differs according to the manufacturer and the specifications of the CCD sensor. Setting the state data enables setting of any timing.

The state data of TG and SSG can be set in TM_A0, A1, A2, A3, and A8.

d. AWB- and AE-detection blocks

The HD49815TF provides automatic white-balance (AWB) and automatic-iris (AE) detection circuits that are indispensable for a camera.

The AWB-detection block takes the R-Y and B-Y color-difference signals completed the color-signal processing, and converts to the R-B and MG-G axes. The converted signals are sent to circuits for the white detection to obtain white signal components only, and the white-color difference value is detected. The 8-bit single-chip microcomputer acquires this detection data, and controls the R and B gains to produce the true white.

The State Data of the AWB detection is AWB_A0 and A8.

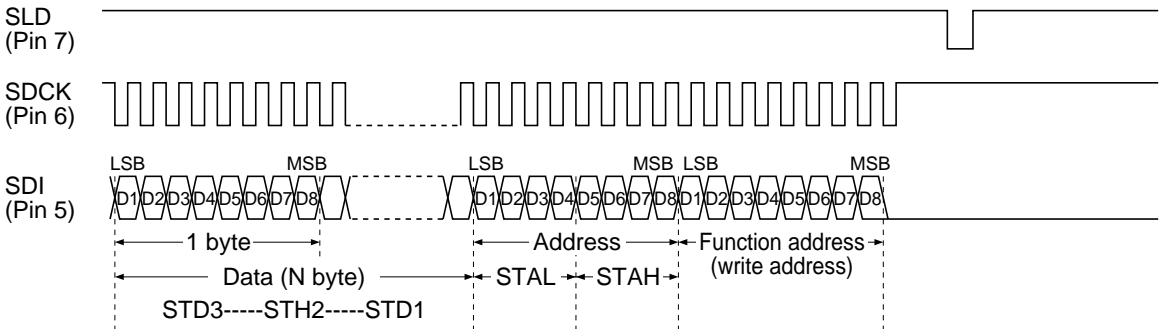
The AE-detection block divides the CCD output signal converted to digital by the 10-bit ADC to six arbitrary areas, and performs integration processing. This function enables detection of the lighting level of the image signal.

The 8-bit single-chip microcomputer acquires this detection data, and controls the accumulation amount (the shutter) of the CCD sensor or the iris motor of the lens to maintain the proper lighting.

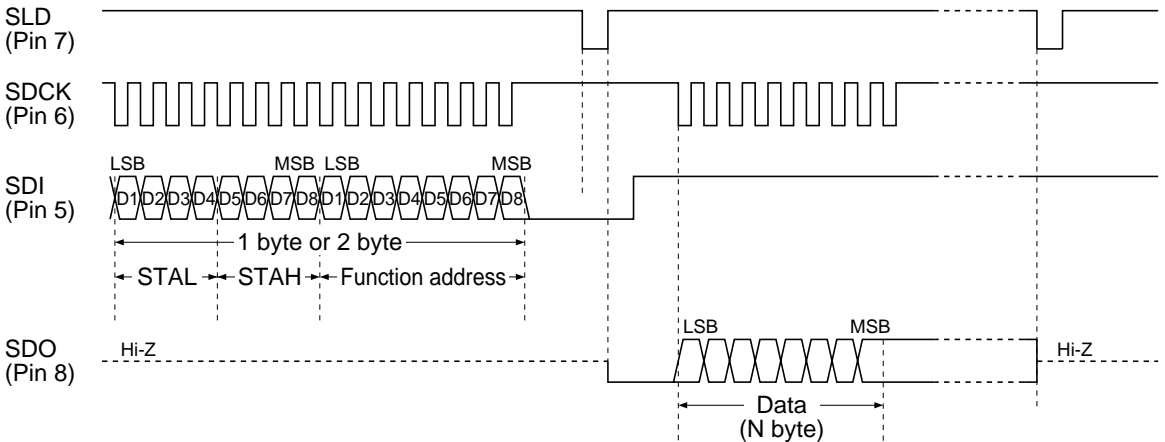
The State Data of the AF detection is AE_A0 to A7 and A8.

Microcomputer Interface Specifications

• Write format



• Read format



- Notes:
1. Synchronous serial transfer (The microcomputer serial port can be used.)
 2. Transfer frequency: 3.58 MHz or lower
 3. Data and address are handled in a byte unit.
 4. The clock and load pulse are used in common for read/write.

Data Transfer Specification

For data transfer between the HD49815TF and the microcomputer, two types (N and E for write, and R1 and R2 for read) are available. The following table shows the relationship between the function block and the transfer specifications. On the next page, the details of the transfer specifications are described.

Function Block	Transfer Mode	Transfer Specifications *1	Related Address
Signal processing	W	N	SP_A0, 2 to 5, 7 to 10, 15
TM	W	N	TM_A3, 15
		E	TM_A0 to 2, 8, 10 to 12
	R	R1	TMR_A0
Iris	W	N	AE_A0 to 7
	R	R2	AE_A8
White balance	W	N	AWB_A0
	R	R1	AWB_A8
AF	W	N	AF_A0 to 3
	R	R1	AF_A8 to 13
ZOOM	W	N	ZM_A0 to 6

Note: 1. Transfer specifications

Type N : Normal transfer from the microcomputer to the DSP

Type E : Transfer using the set pulse (synchronous with VD) or the reset signal (used as a synchronous pulse in the DSP) sent from the microcomputer to the RS latch in the DSP

Note: This cannot be set during the standby mode.

Type R1 : Data transfer (1) from the DSP to microcomputer

Type R2 : Data transfer (2) from the DSP to microcomputer

- Type N

Transfer specification	Pulse Timing	Conditions
N		<p>A = 100 ns or more B = 100 ns or more C = 100 ns or more</p>

- Type E

Transfer specification	Pulse Timing	Conditions		
E		A	B	D
			270,000 pixels	410,000 pixels
		0.5 / fs + 100 ns or more	150 ns or more	135 ns or more
		2 / fs + 100 ns or more	300 ns or more	240 ns or more
		5.5 / fs + 100 ns or more	650 ns or more	485 ns or more
		fs	Sensor clock	100 ns / 70 ns

- Type R1

Transfer specification	Pulse Timing	Conditions
R1		<p>A = 100 ns or more B = 100 ns or more D = 400 ns or more</p> <p>Do not read the white balance data and the AF read data within the 1H period from the start of the V blanking.</p>

- Type R2

Transfer specification	Pulse Timing	Conditions		
R2		A	B	D
		<p>A = 100 ns or more B = 100 ns or more</p>		
			270,000 pixels	410,000 pixels
		D	{1 / fs × (32 + 5) + 400 ns} or more	4.1 μs or more / 2.99 μs or more
		fs	Sensor clock	100 ns / 70 ns

Note: 2 to 9. Function addresses

The following table shows the function addresses for each function block (during state data transfer) and the data to be transferred from the microcomputer.

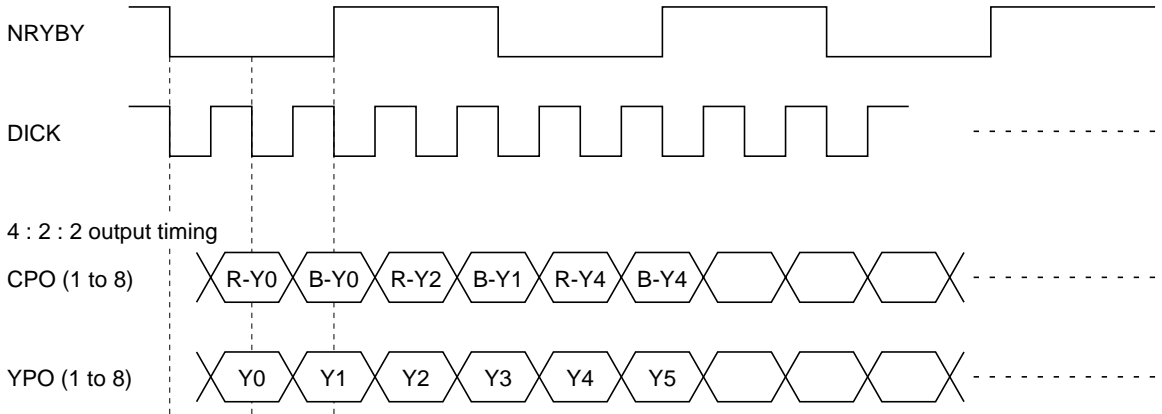
Table 2 Function Addresses for each Function Block and State Data

		List of Data Transferred																Remarks																									
2	Signal processing (Setting example)	Function Address								STAH				STAL				STD1				STD2				This example is related to SP-A0[9].																	
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	0	0	0	0	0	0	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*		*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	
3	TM write (Setting example)	Function Address								STAH				STAL				STD1				STD2				This example is related to TM-A0 [14].																	
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	0	0	0	0	0	1	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*		*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	
4	TM read	Function Address								Data read for automatic phase adjustment for SP1, SP2, and RG																																	
		D8	D7	D6	D5	D4	D3	D2	D1																																		
		0	0	0	0	1	0	0	1																																		
5	AE	Function Address								ADATA				STAH				STAL				STD1				STD2				This example is related to the IRIS peak detection area.													
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5		D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	0	1	0	*	*	*	*	*	*	*	*	*	*	*	—	—	—	*	*	*	*	0	0	0	0	0		0	0	0	0	0	0	0	0	0	0	0		
		Function Address								ADATA				STAH				STAL				STD1				STD2				This example is related to the window H count 3.													
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5		D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	0	0	0	0	0	1	*	*	*	*	*	*	*	*	—	—	—	*	*	*	*	0	0	0	0	0		0	0	0	0	0	0	0	0	0	0	0		
6	R	Function Address								STAH				STAL				Read area setting by STAL (4 bits)																									
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1																										
		0	0	0	1	1	0	0	0	—	—	—	*	*	*	*																											
7	AWB	Function Address								ADATA				STAH				STAL				STD1				STD2				This example is related to the offset R-B.													
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5		D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	1	0	0	—	—	—	—	—	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	0	0		0	0	0	0	0	0	0	0	0	0	0	0	0
		Function Address								ADATA				STAH				STAL				STD1				STD2				This example is related to the V count 2.													
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5		D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	0	0	0	0	0	*	*	*	*	*	*	*	*	—	—	*	*	*	*	*	*	*	*	*	*	*		*	0	0	0	0	0	0	0	0				
8	R	Function Address								White balance read																																	
		D8	D7	D6	D5	D4	D3	D2	D1																																		
		0	0	1	0	1	0	0	0																																		
9	AF	Function Address								ADATA				STAH				STAL				STD1				STD2				This example is related to the HRF bandwidth selection.													
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5		D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	1	1	0	*	*	*	*	*	*	*	*	*	*	—	—	*	*	*	*	*	*	*	*	*	*	*		*	0	0	0	0	0	0	0	0				
		Function Address								ADATA				STAH				STAL				STD1				STD2				This example is related to the differential gate of V-end.													
		D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	D8	D7	D6	D5		D4	D3	D2	D1	D8	D7	D6	D5	D4	D3	D2	D1	
		0	0	0	0	0	0	0	1	1	1	0	0	0	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*		*	0	0	0	0	0	0	0	0				
10	R	Function Address								Vf fetch address (read_cycle)																																	
		D8	D7	D6	D5	D4	D3	D2	D1																																		
		0	0	1	1	1	*	*	*																																		
ZOOM	W	Header								Data 1				Data 2				Data 3																									
		D8	D7	D6	D5	D4	D3	D2	D1																																		
		1	0	1	1	0	*	*	*																																		
										Data 4				Data 5				Data 6																									

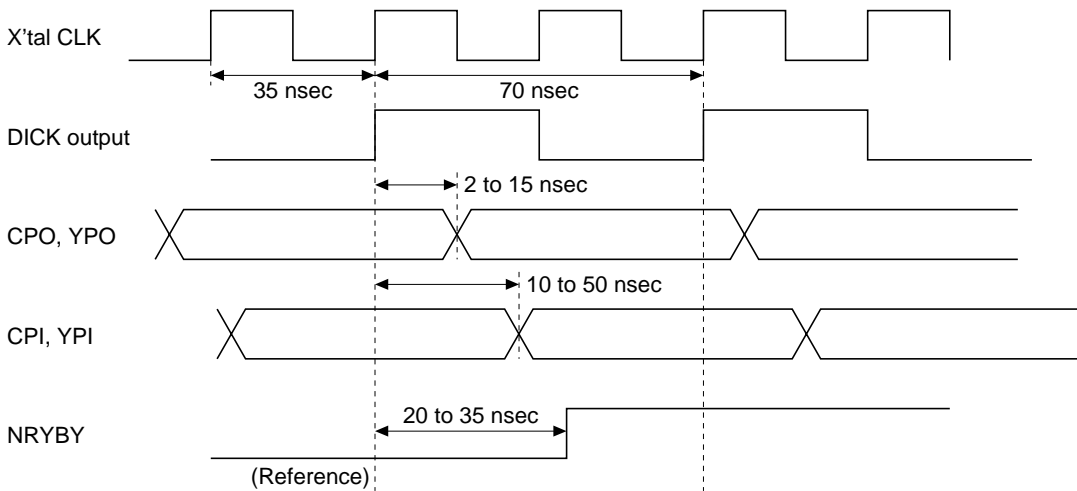
Note: For the ZOOM, the transfer of in total of seven bytes is required for the header and data 1 to 6.

Digital Interface Timing

- The output specification and timing of the digital interface output (Y, R-Y, B-Y)



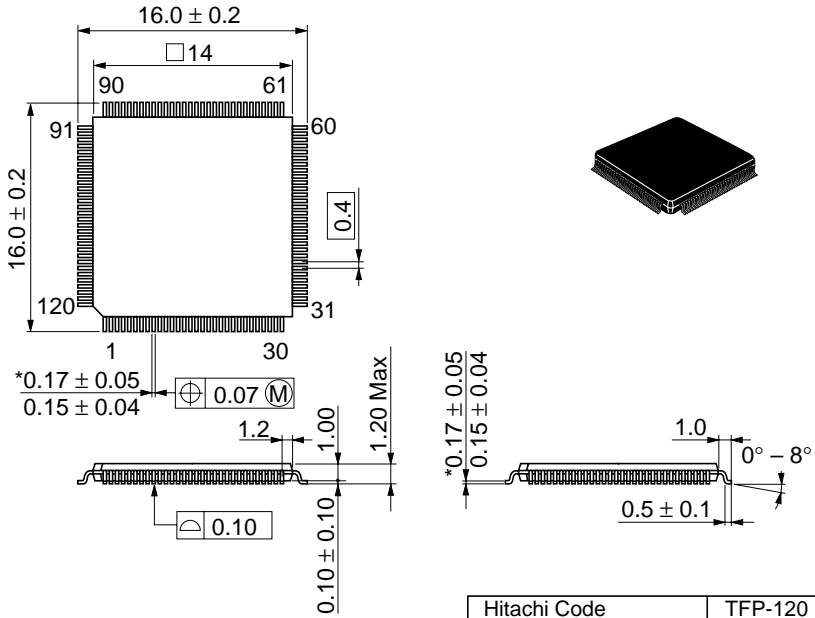
- Detailed specifications of digital interface timing



- NRYBY : R-Y/B-Y determination pulse
- DICK : Clock dedicated to the digital interface (The clock generated from the external X'tal.)
- CPO, YPO : Digital interface output terminal
- CPI, YPI : Digital interface input terminal

Package Dimensions

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TFP-120
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.5 g

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